



TECHNICAL DATA

ULTRAFAST SILICON POWER RECTIFIER

Qualified per MIL-PRF-19500/646

Devices

1N6774 1N6775 1N6776 1N6777

Qualified Level

JAN
JANTX
JANTXV

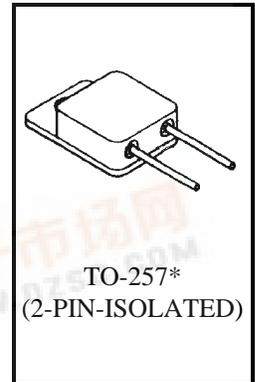
MAXIMUM RATINGS

Ratings	Symbol	1N6774	1N6775	1N6776	1N6777	Unit
Working Peak Reverse Voltage	V_{RWM}	50	100	150	200	Vdc
Forward Current $T_C = +100^{\circ}C^{(1)}$	I_F	15				Adc
Forward Current Surge Peak $T_P = 8.3^{\circ}C$	I_{FSM}	180				Apk
Operating & Storage Junction Temperature	T_{op}, T_{stg}	-65 to +150				$^{\circ}C$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.0	$^{\circ}C/W$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	40	$^{\circ}C/W$

1) Derate at 300 mA/ $^{\circ}C$ above $T_C = +100^{\circ}C$



*See appendix A for package

ELECTRICAL CHARACTERISTICS ($T_C = +25^{\circ}C$ Unless Otherwise Noted)

outline

Characteristics	Symbol	Min.	Max.	Unit
Forward Voltage $I_F = 8.0$ Adc, pulsed $I_F = 15$ Adc, pulsed	V_F		1.00 1.15	Vdc
Reverse Current Leakage $V_R = 0.8$ of V_{RWM}	I_R		10	μ Adc
Thermal Impedance $I_M = 15$ mAdc; $I_H = 9.9$ Adc; $t_H = 200$ ms; $t_{MD} = 35$ μ s; $V_H = 1$ Vdc	$Z_{\theta JX}$		1.8	$^{\circ}C/W$
Breakdown Voltage $I_R = 10$ μ Adc	V_{BR}		50 100 150 200	Vdc
Junction Capacitance $V_R = 5.0$ Vdc, $f = 1.0$ MHz	C_J		300	pF
Reverse Recovery Time $I_F = 1.0$ Adc; $di/dt = 50$ A/ μ s	t_{rr}		35	η s

